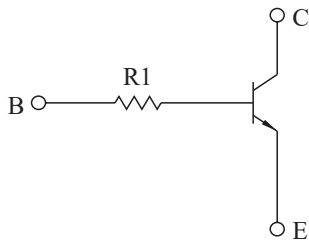


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

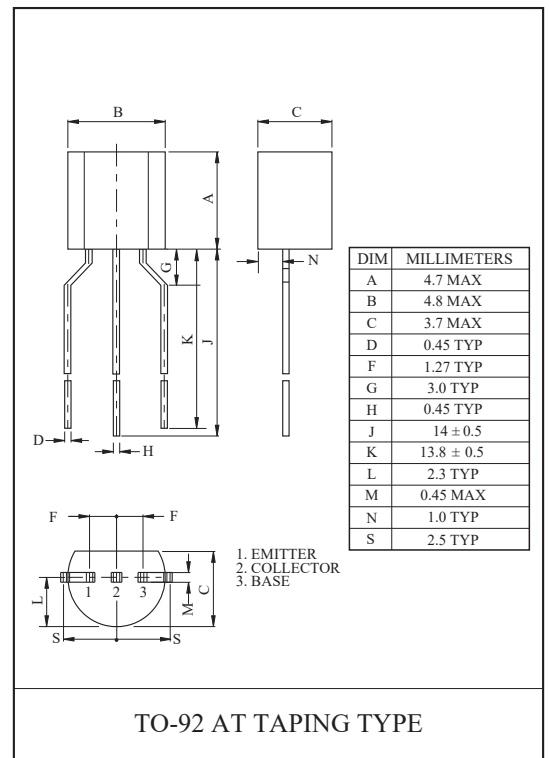
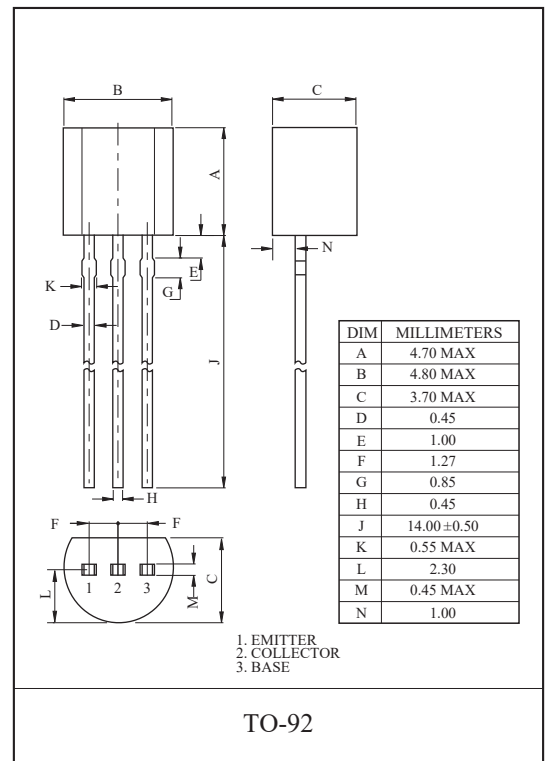
- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT



MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	-55~150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



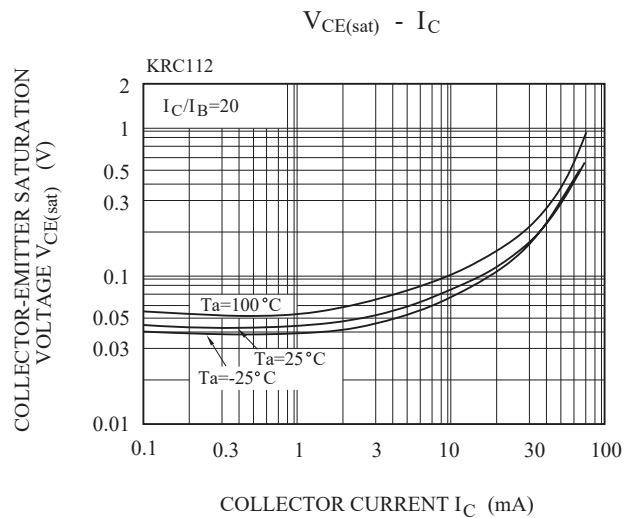
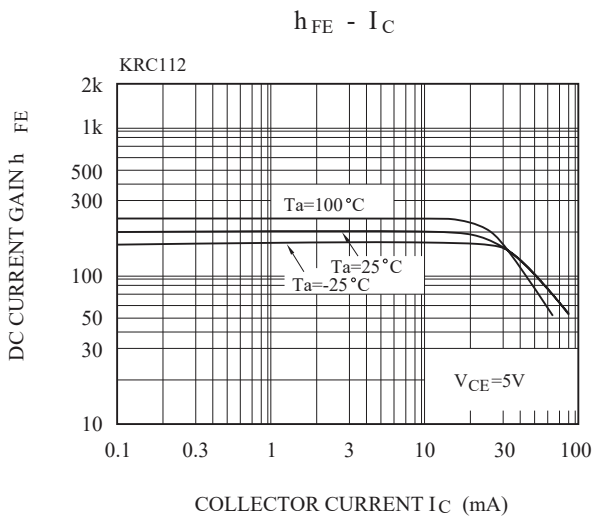
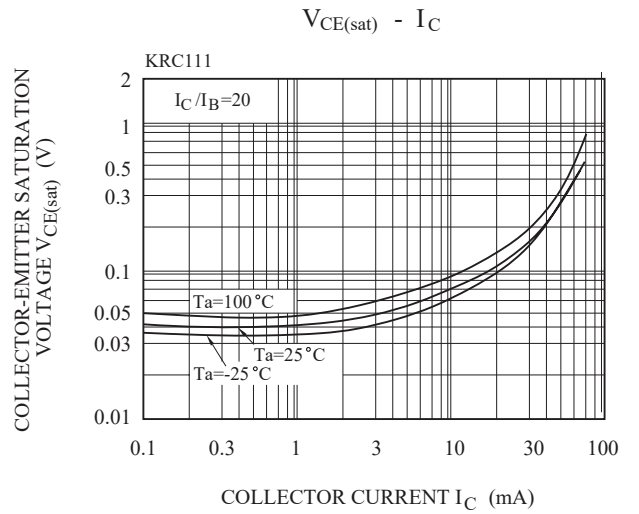
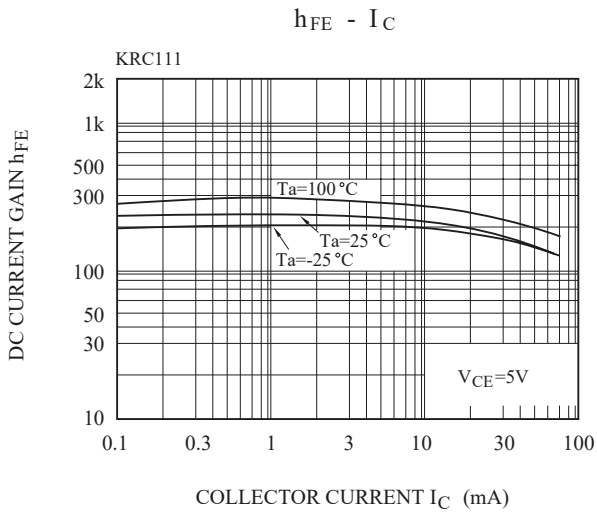
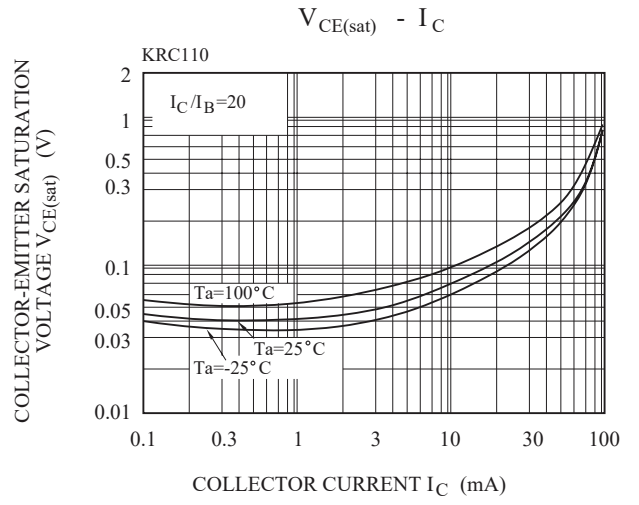
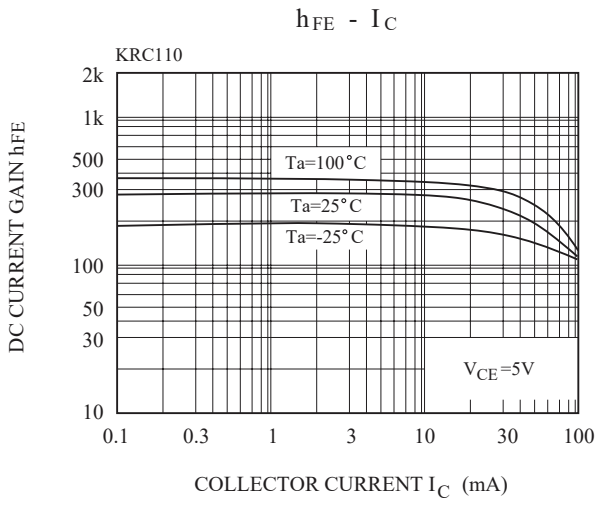
KRC110~KRC114

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Collector Cut-off Current		I_{CBO}	$V_{CB}=50V, I_E=0$	-	-	100	nA		
Emitter Cut-off Current		I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	100	nA		
DC Current Gain		h_{FE}	$V_{CE}=5V, I_C=1mA$	120	-	-			
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=10mA, I_B=0.5mA$	-	0.1	0.3	V		
Transition Frequency		f_T^*	$V_{CE}=10V, I_C=5mA$	-	250	-	MHz		
Switching Time	Rise Time	KRC110	t_r	$V_O=5V$ $V_{IN}=5V$ $R_L=1k\Omega$	-	0.025	-	μS	
		KRC111			-	0.03	-		
		KRC112			-	0.3	-		
		KRC113			-	0.06	-		
		KRC114			-	0.11	-		
	Storage Time	KRC110			t_{stg}	-	3.0		-
		KRC111			-	-	2.0		-
		KRC112			-	-	6.0		-
		KRC113			-	-	4.0		-
		KRC114			-	-	5.0		-
	Fall Time	KRC110			t_f	-	0.2		-
		KRC111			-	-	0.12		-
		KRC112			-	-	2.0		-
		KRC113			-	-	0.9		-
		KRC114			-	-	1.4		-
Input Resistor		KRC110	R_1	-	3.29	4.7	6.11	k Ω	
		KRC111			7	10	13		
		KRC112			70	100	130		
		KRC113			15.4	22	28.6		
		KRC114			32.9	47	61.1		

Note : * Characteristic of Transistor Only.

KRC110~KRC114



KRC110~KRC114

